B 14216.3 ID



Declaration, Power Of Attorney and Petition

Page 1 of 3

WU (I) the undersigned inventor(s), hereby declare(s) that:

My residence, post office address and citizenship are as stated below next to my name,

We (I) believe that we are (I am) the original, first, and joint (sole) inventor(s) of the subject matter which is claimed and for which a patent is sought on the invention entitled A METHOD FOR FORMING, BY CVD, NANOSTRUCTURES OF SEMI-CONDUCTOR MATERIAL OF HOMOGENEOUS AND CONTROLLED SIZE ON DIELECTRIC MATERIAL

the specification of which				
is attached hereto.				
was filed on November 19, 2003				
as Application Serial No. 10/718,109				
and amended on				
was filed as PCT international application				
Number				
on				
and was amended under PCT Article 19				
on				

- We (I) hereby state that we (I) have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.
- We (I) acknowledge the duty to disclose information known to be material to the patentability of this application as defined in Section 1.56 of Title 37 Code of Federal Regulations.
- We (I) hereby claim foreign priority benefits under 35 U.S.C. § 119 (a)-(d) or § 365 (b) of any foreign application(s) for patent or inventor's certificate, or § 365 (a) of any PCT International application which designated at least one country other than the United States, listed below and have also identified below, by checking the box, any foreign application for patent or inventor's certificate, or PCT International application having a filing date before that of the application on which priority is claimed. Prior Foreign Application (s)

Application No.	Country	Day/month/Year	Priority Claimed
02 14658	FRANCE	22.11.2002	⊠ YES □ NO
			YES NO

We (I) hereby claim the berapplication(s) listed below.	nefit under Title 35, United S	States Code, § 119 (e) of any	United States provisional
-	(Application Number)	(Filin	g Date)
	(Application Number)	•	ng Date)
International application designation designation is not disclose	mating the United States, in the prior United States	or PCT International application	application(s), or § 365(c) of any PCT e subject matter of each of the claims of ation in the manner provided by the first material to patentability as defined in 37 the national or PCT International filing
Application Serie	al No.	Filing Date	Status (pending, patented, abandoned)
S. Hanish, Registration No. 43,186; Adrienne Yeung, Re No. 49,097; William Samue (my) attorneys of record w business in the United Star correspondence regarding the Address is: P.O. Box 64064 We (I) declare that all s information and belief are b false statements and the like United States Code and that thereon.	gistration No. 44,000; Steve 1 Niece, Registration No.: I ith full power of substituti tes Patent and Trademark his application be sent to 0, San Jose, CA 95164-0646 statements made herein of calieved to be true; and furth	on J. Robbins, Registration NP47,824; and John Klaas Uion and revocation, to prose Office connected therewith the firm of THELEN REID Dur (my) own knowledge are that these statements were	titchie, Registration No. 31,562; Marc rhard W. Thielman, Registration No. 0. 40,299; Thierry K. Lo, Registration ilkema, Registration No. 20,282; our cute this application and transact all; and we (I) hereby request that all & PRIEST LLP whose Post Office true and that all statements made on a made with the knowledge that willful a, under Section 1001 of Title 18 of the of the application or any parent issuing
MAZEN Frédéric NAMÉ OF FIRST SO Signature of Inventor	FRU	TO CE	15 me René 38000 Cromobile FRANCE

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	Residence:
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_	Citizen of:
Signature of Inventor	Post Office Address: The same as residence
Date .	